International
IOR Rectifier

4GBU Series

4.0 Amps Single Phase Full Wave Bridge Rectifier

Features

- Diode chips are glass passivated
- Suitable for Universal hole mounting
- Easy to assemble & install on P.C.B.
- High Surge Current Capability
- High Isolation between terminals and molded case (1500 V_{RMS})
- Lead free terminals solderable as per MIL-STD-750 Method 2026
- Terminals suitable for high temperature soldering at 260°C for 8-10 secs
- UL E215862 approved

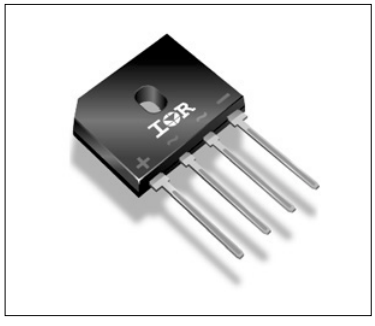
$I_{O(AV)}$ = 4A
V_{RRM} = 50/ 800V

Description

These GBU Series of Single Phase Bridges consist of four glass passivated silicon junction connected as a Full Wave Bridge. These four junctions are encapsulated by plastic molding technique. These Bridges are mainly used in Switch Mode power supply and in industrial and consumer equipment.

Major Ratings and Characteristics

Parameters		4GBU	Units
I_O		4	A
	@ T_C	100	°C
I_{FSM}	@50Hz	150	A
	@60Hz	158	A
I^2t	@50Hz	113	A^2s
	@60Hz	104	A^2s
V_{RRM}	range	50 to 800	V
T_J		- 55 to 150	°C



4GBU

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM}, max repetitive peak rev. voltage $T_J = T_J$ max. V	V_{RMS}, max RMS voltage $T_J = T_J$ max. V	I_{RRM} max. @ rated V_{RRM} T_J = 25°C µA	I_{RRM} max. @ rated V_{RRM} T_J = 150°C µA
4GBU	005	50	35	5	400
4GBU...F	01	100	70	5	400
	02	200	140	5	400
	04	400	280	5	400
	06	600	420	5	400
	08	800	560	5	400

Forward Conduction

	Parameters	4GBU	Unit	Conditions	
I_O	Maximum DC output current	4	A	T_C = 100°C, Resistive & inductive load	
		3.2		T_C = 100°C, Capacitive load	
I_{FSM}	Maximum peak, one-cycle non-repetitive surge current, following any rated load condition and with rated V_{RRM} reapplied	150		t = 10ms	T_J = 150°C
		158		t = 8.3ms	
I^2t	Maximum I^2t for fusing, initial $T_J = T_J$ max	113	A^2s	t = 10ms	
		104		t = 8.3ms	
V_{FM}	Maximum peak forward voltage per diode	1.0	V	T_J = 25°C, I_{FM} = 4A	
I_{RM}	Typical peak reverse leakage current per diode	5	µA	T_J = 25°C, 100% V_{RRM}	
V_{RRM}	Maximum repetitive peak reverse voltage range	50 to 800	V		

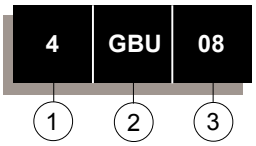
Thermal and Mechanical Specifications

	Parameters	4GBU	Unit	Conditions
T_J T_{stg}	Operating and storage temperature range	-55 to 150	°C	
R_{thJC}	Max. thermal resistance junction to case	4.2	°C/W	DC rated current through bridge (1)
R_{thJA}	Thermal resistance, junction to ambient	22	°C/W	DC rated current through bridge (1)
W	Approximate weight	4 (0.14)	g (oz)	
T	Mounting Torque	1.0	Nm	Bridge to Heatsink
		9.0	Lb.in	

Note (1): Devices mounted on 40x 40x1.5mm aluminum plate; use silicon thermal compound for maximum heat transfer and bolt down using 3mm screw

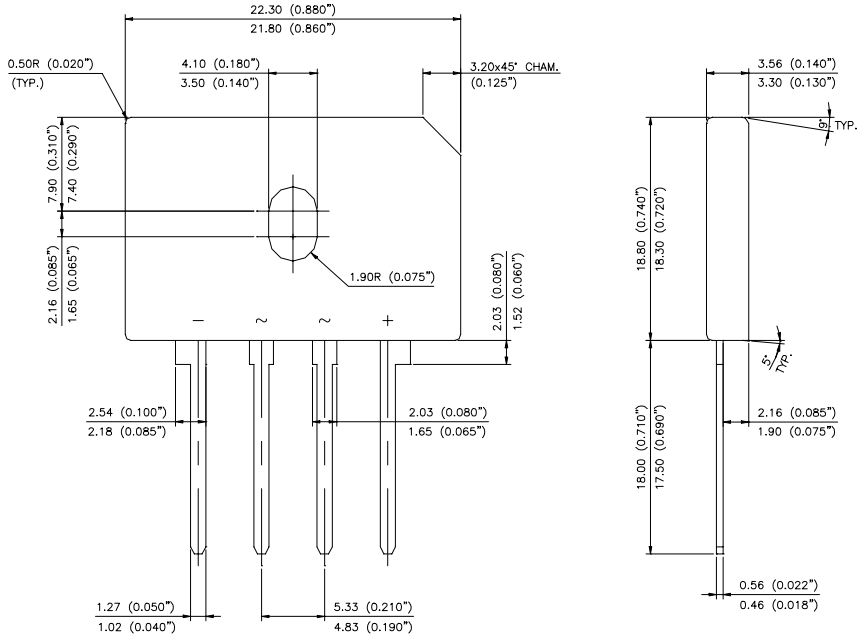
Ordering Information Table

Device Code



1	-	Bridge current
2	-	Basic Part Number
3	-	Voltage Code: code x 100 = V_{RRM}

Outline Table



NOTE:
1. POLARITY SHOWN ON FRONT SIDE OF CASE, POSITIVE LEAD BY BEVELED CORNER
2. ALL DIMENSIONS IN MM AND (INCHES)

Add suffix "F" for 7.5 mm equal space lead forming

All dimensions are in millimeters

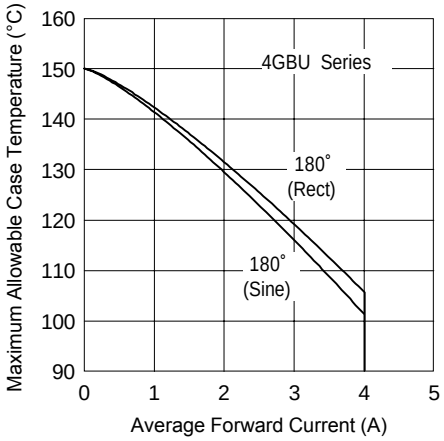


Fig. 1 - Current Ratings Characteristics

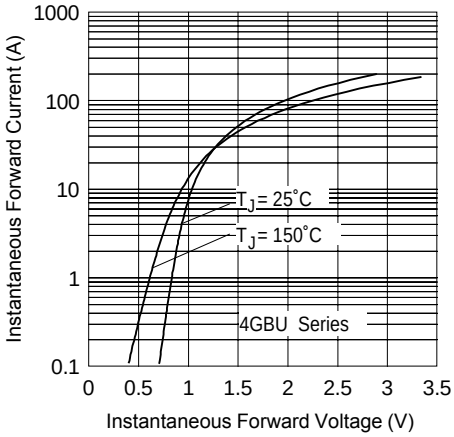


Fig. 2 - Forward Voltage Drop Characteristics

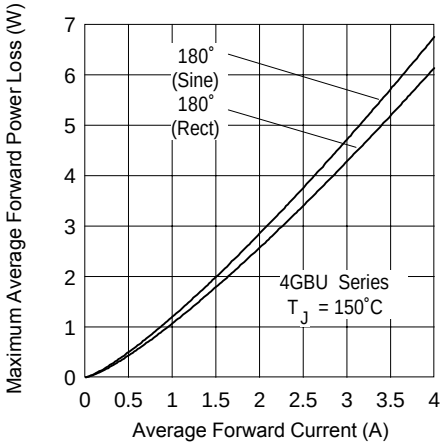


Fig. 3 - Total Power Loss Characteristics

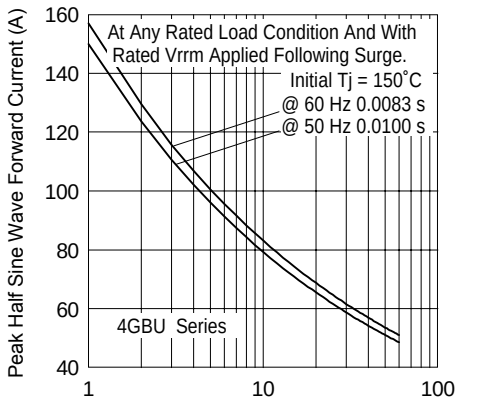


Fig. 4 - Maximum Non-Repetitive Surge Current

Data and specifications subject to change without notice.
This product has been designed and qualified for Multiple Level.
Qualification Standards can be found on IR's Web site.

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